

Advanced Analog Building Blocks

Transistor Level Logic



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Digital logic are in fact analog circuits

Yes that's true!!

- Set of "basic blocks" grouped in Standard Cells.
- CMOS: Complementary metal-oxide-semiconductor, from complementary structures in logic.
- Standard Cells have several constrains/characteristics;
 - Fixed height and variable width.
 - Fixed position of VDD and GND.
- Set of important characteristics;
 - Delay/speed.
 - Power consumption.
 - Driving power.

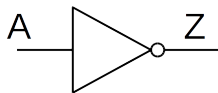
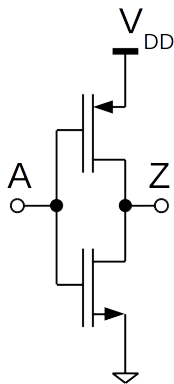


- Rising/falling edge:
 - **Designed to have same rising and falling time at output!!**
- Driving power:
 - Is measured as integer values of how much simple inverters the cell can drive.
 - Naming convention: INV1, INV2,... AND1,AND2,...



Combinational logic: Inverter

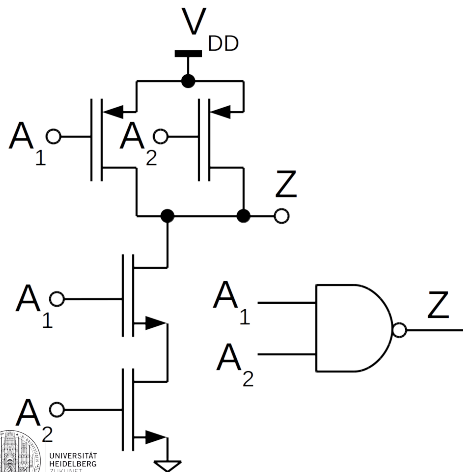
Simpler cell is an inverter (remember amplifiers?).



A	Z
0	1
1	0

Combinational logic: NAND gate

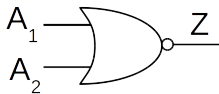
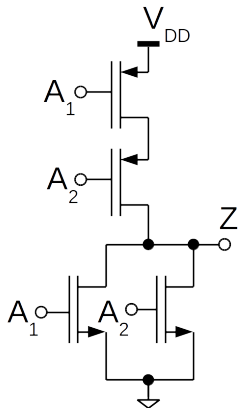
NAND Gate:



A_1	A_2	Z
0	0	1
0	1	1
1	0	1
1	1	0

Combinational logic: NOR gate

NOR Gate:

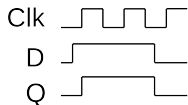
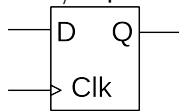
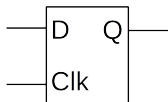


A_1	A_2	Z
0	0	1
0	1	0
1	0	0
1	1	0

All other combinational functions can be generated using previous elements.

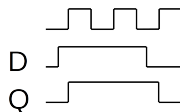


Of course sequential cells can also be used/implemented;



Latch stores

data when clock low.



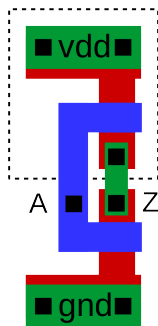
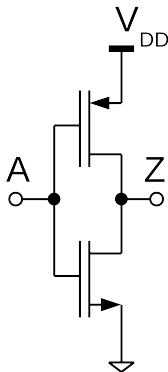
Register stores






data when clock rises.

More constraints added, setup/hold time for clocked systems.



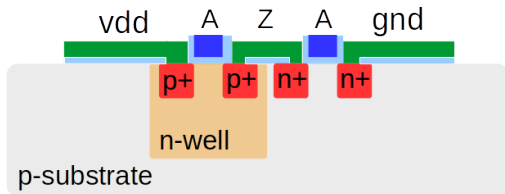
Standard cell example: Inverter



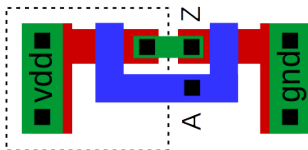
-  METAL
-  POLYSILICON
-  DIFFUSION
-  CONTACT
-  N-WELL



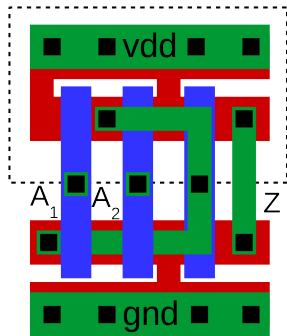
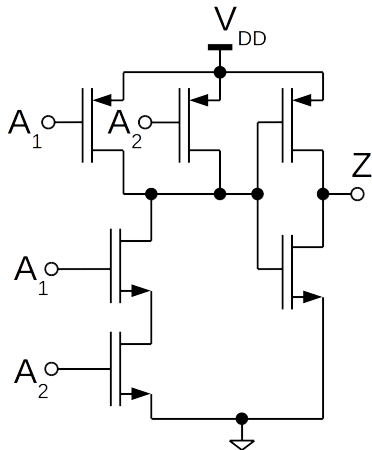
Inverter Cross section



- OXIDE
- METAL
- POLYSILICON
- DIFFUSION
- CONTACT
- N-WELL



Standard cell example: AND gate

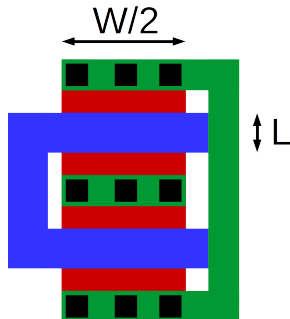
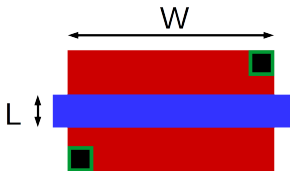


- METAL
- POLYSILICON
- DIFFUSION
- CONTACT
- N-WELL

Layout of Standard cells

- Transistors use minimum Length usually.
- Effective R scales linearly with $1/W$.
- Gate capacitance scales linearly with W .
- Diffusion capacitance scales linearly with W .

Some recommendation for long transistors:

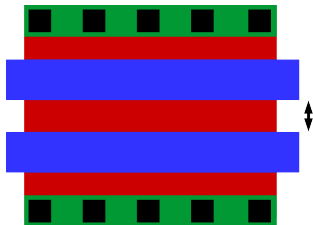


- Long transistors have large diffusion C.

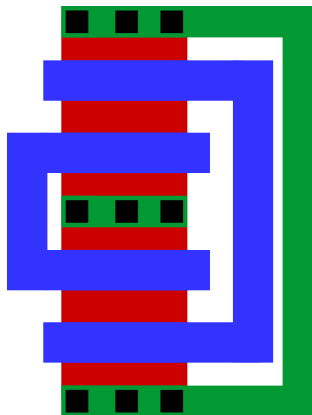
- Folded reduces diffusion C,

Layout of Standard cells

Some recommendation for long transistors:



- Series transistors as close as possible reduce R and C parasitics.

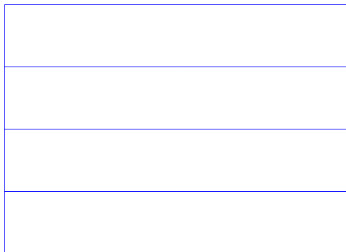


- Folded stack not individual transistors.

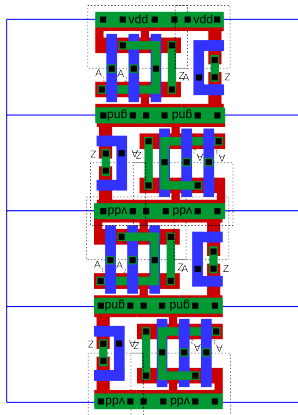


Place and route

- Digital tools start with defining a grid for placement;



- Cells are placed at each row with interleaved rotation.
- Metals are routed in horizontal and vertical directions.



Modern standard cells

- Modern technologies provide different "flavours" of standard cells.
- They can be combined by synthesis tools depending on constraints.
- Use of different types of transistors;
 - Regular-Voltage-Threshold (STD)
 - Used as default/reference.
 - High-Voltage-Threshold (HVT)
 - Slower.
 - Less power consumption.
 - Low-Voltage-Threshold (LVT)
 - Faster.
 - More power consumption.



Exercise 1: Standard cells design

Design an AND gate with following requirements;

- Same rising/falling time.
- Driving power = 1 (an inverter must be designed also).
- Minimum size as possible.

Are the rising/falling times equal in MonteCarlo?

Can you fit it in $3\mu m$ height?